

## Modification of single ion anisotropy in epitaxial $Mn_5Ge_3/Ge(111)$ films by carbon doping



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## Introduction

 $Mn_5Ge_3$  is a very interesting compound with potential for application in spintronic devices. Numerous advantages of this compound, like high spin polarization (42%), easy fabrication, high Curie temperature ( $T_c$  = 296 K), which can be further increased up to 445 K by addition of small amount of carbon, as well as full compatibility with Si and Ge based technology, make it one of the best candidates to incorporate into conventional Si-based electronic devices. To investigate the anisotropic properties of  $Mn_5Ge_3$ epitaxial thin films, we performed a thorough study using <sup>55</sup>Mn NMR (Nuclear Magnetic Resonance) technique. This technique belongs to the advanced characterization methods and can yield a unique magnetic and structural information on the nanoscale.



Crystal structure of  $Mn_5Ge_3C_x$  phase with interstitial carbon at x=1 (full occupancy) of carbon): a) projection on xy – plane and b) side view [ref 1].

